

- Designed for Complementary Use with the TIP30 Series
- 30 W at 25°C Case Temperature
- 1 A Continuous Collector Current
- 3 A Peak Collector Current
- Customer-Specified Selections Available

TO-220 PACKAGE

Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	TIP29		80		
Collector-base voltage (I _E = 0)	TIP29A	V	100	V	
	TIP29B	V _{CBO}	120	٧	
	TIP29C		140		
	TIP29		40		
Callector emitter voltage (I = 0)	TIP29A	V	60	V	
Collector-emitter voltage (I _B = 0)	TIP29B	V _{CEO}	80		
	TIP29C		100		
Emitter-base voltage			5	V	
Continuous collector current			1	Α	
Peak collector current (see Note 1)	I _{CM}	3	Α		
Continuous base current			0.4	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			30	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			2	W	
Unclamped inductive load energy (see Note 4)			32	mJ	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range			-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds			250	°C	

NOTES: 1. This value applies for $t_p \le 0.3$ ms, duty cycle $\le 10\%$.

- 2. Derate linearly to 150°C case temperature at the rate of 0.24 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = 0.4 A, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = 20 V.



electrical characteristics at 25°C case temperature

PARAMETER			TEST CONDITIONS			TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = 30 mA (see Note 5)	I _B = 0	TIP29 TIP29A TIP29B TIP29C	40 60 80 100			V
I _{CES}	Collector-emitter cut-off current	$V_{CE} = 80 \text{ V}$ $V_{CE} = 100 \text{ V}$ $V_{CE} = 120 \text{ V}$ $V_{CE} = 140 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIP29 TIP29A TIP29B TIP29C			0.2 0.2 0.2 0.2	mA
I _{CEO}	Collector cut-off current	V _{CE} = 30 V V _{CE} = 60 V	I _B = 0 I _B = 0	TIP29/29A TIP29B/29C			0.3 0.3	mA
I _{EBO}	Emitter cut-off current	V _{EB} = 5 V	I _C = 0				1	mA
h _{FE}	Forward current transfer ratio	$V_{CE} = 4 V$ $V_{CE} = 4 V$	$I_C = 0.2 A$ $I_C = 1 A$	(see Notes 5 and 6)	40 15		75	
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = 125 mA	I _C = 1 A	(see Notes 5 and 6)			0.7	٧
V _{BE}	Base-emitter voltage	V _{CE} = 4 V	I _C = 1 A	(see Notes 5 and 6)			1.3	>
h _{fe}	Small signal forward current transfer ratio	V _{CE} = 10 V	$I_{\rm C} = 0.2 \; {\rm A}$	f = 1 kHz	20			
h _{fe}	Small signal forward current transfer ratio	V _{CE} = 10 V	I _C = 0.2 A	f = 1 MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu s$, duty cycle $\leq 2\%$.

thermal characteristics

PARAMETER			TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			4.17	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = 1 A	I _{B(on)} = 0.1 A	$I_{B(off)} = -0.1 \text{ A}$		0.5		μs
t _{off}	Turn-off time	$V_{BE(off)} = -4.3 \text{ V}$	$R_L = 30 \Omega$	$t_p = 20 \ \mu s, \ dc \le 2\%$		2		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN VS COLLECTOR CURRENT TCS631AD TCS631AD

Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE

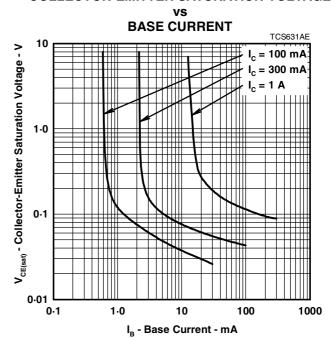


Figure 2.

BASE-EMITTER VOLTAGE

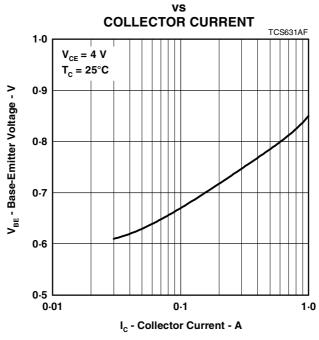
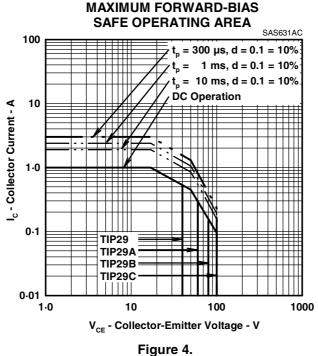


Figure 3.

MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

MAXIMUM POWER DISSIPATION

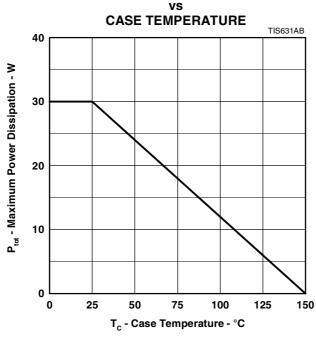


Figure 5.

PRODUCT INFORMATION